PNP Silicon Digital Transistor
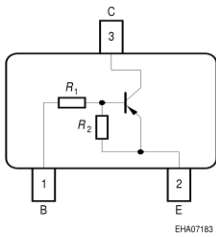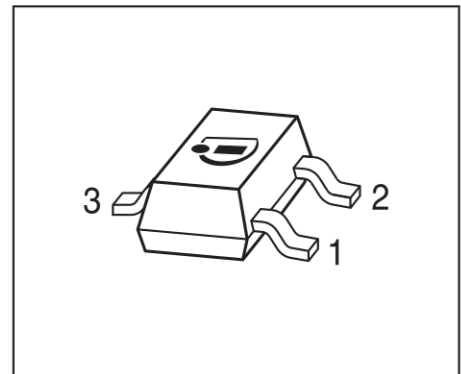
- Built in bias resistor (R_1= 10 kΩ, R_2= 10 kΩ)

- Pb-free (RoHS compliant) package

- Qualified according AEC Q101

Type	Marking	Pin Configuration			Package
BCR583	XMs	1=B	2=E	3=C	SOT23

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Input forward voltage	$V_{i(fwd)}$	50	
Input reverse voltage	$V_{i(rev)}$	10	
Collector current	I_C	500	mA
Total power dissipation- $T_S \leq 79\ °C$	P_{tot}	330	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[1]	R_{thJS}	≤ 215	K/W

[1]For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage I_C = 100 µA, I_B = 0	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage I_C = 10 µA, I_E = 0	$V_{(BR)CBO}$	50	-	-	
Collector-base cutoff current V_{CB} = 50 V, I_E = 0	I_{CBO}	-	-	100	nA
Emitter-base cutoff current V_{EB} = 10 V, I_C = 0	I_{EBO}	-	-	0.75	mA
DC current gain- I_C = 50 mA, V_{CE} = 5 V	h_{FE}	70	-	-	-
Collector-emitter saturation voltage[1] I_C = 50 mA, I_B = 2.5 mA	V_{CEsat}	-	-	0.3	V
Input off voltage I_C = 100 µA, V_{CE} = 5 V	$V_{i(off)}$	0.6	-	1.5	
Input on voltage I_C = 10 mA, V_{CE} = 0.3 V	$V_{i(on)}$	1.1	-	2.5	
Input resistor	R_1	7	10	13	kΩ
Resistor ratio	R_1/R_2	0.9	1	1.1	-
AC Characteristics					
Transition frequency I_C = 50 mA, V_{CE} = 5 V, f = 100 MHz	f_T	-	150	-	MHz

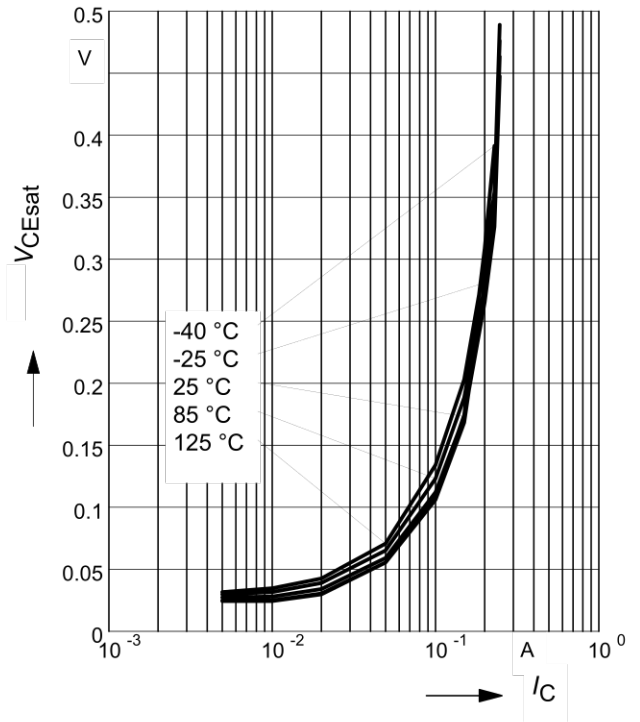[1]Pulse test: t < 300µs; D < 2%

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DC current gain $h_{FE} = f(I_C)$

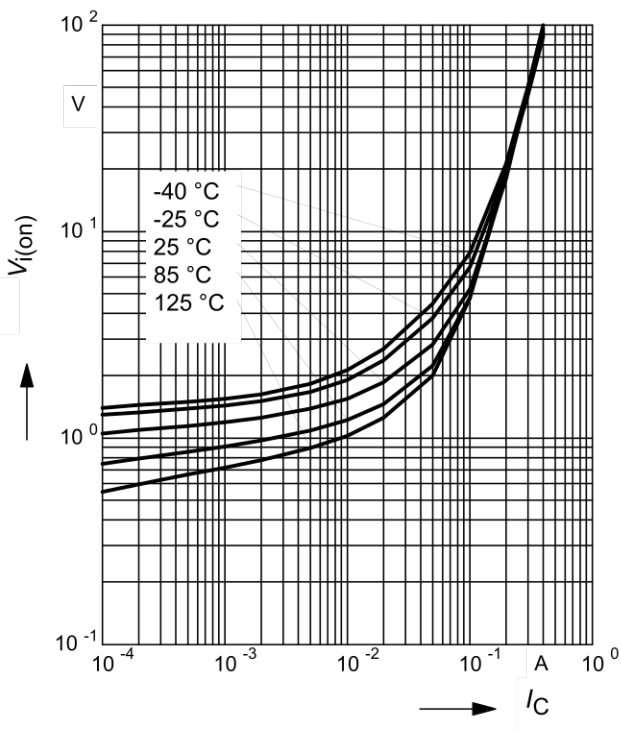$V_{CE} = 5$ V (common emitter configuration)

Collector-emitter saturation voltage
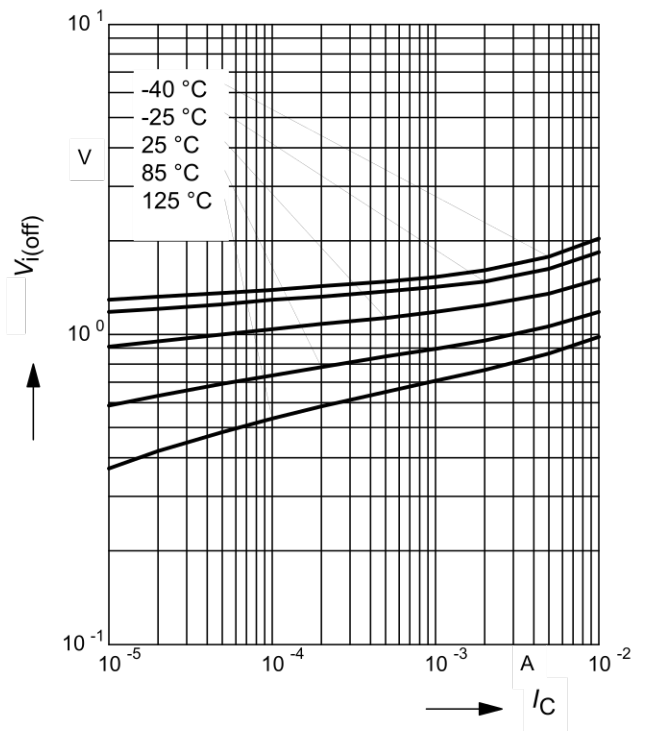
$V_{CEsat} = f(I_C)$, $h_{FE} = 20$

Input on Voltage $V_{i(on)} = f(I_C)$
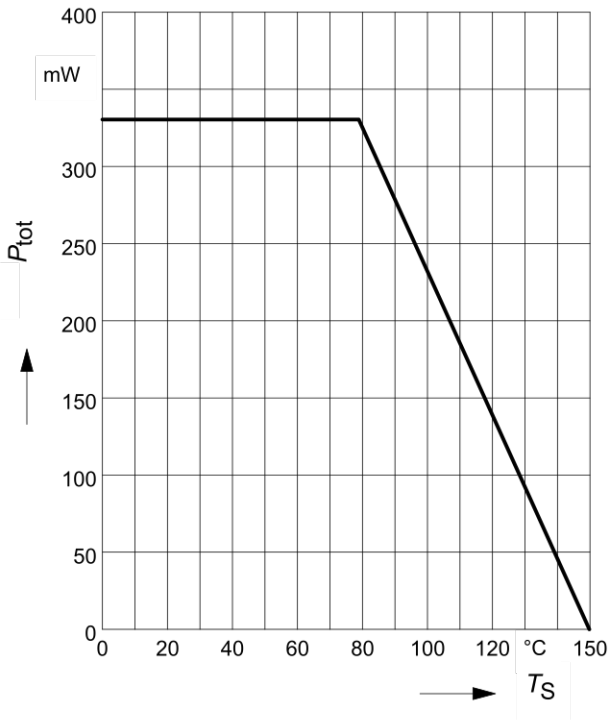
$V_{CE} = 0.3$V (common emitter configuration)

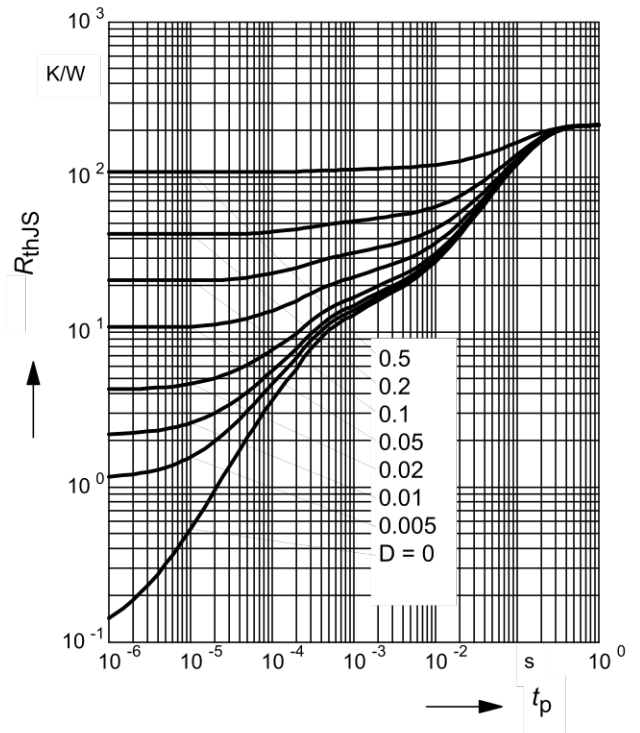
Input off voltage $V_{i(off)} = f(I_C)$

$V_{CE} = 5$V (common emitter configuration)
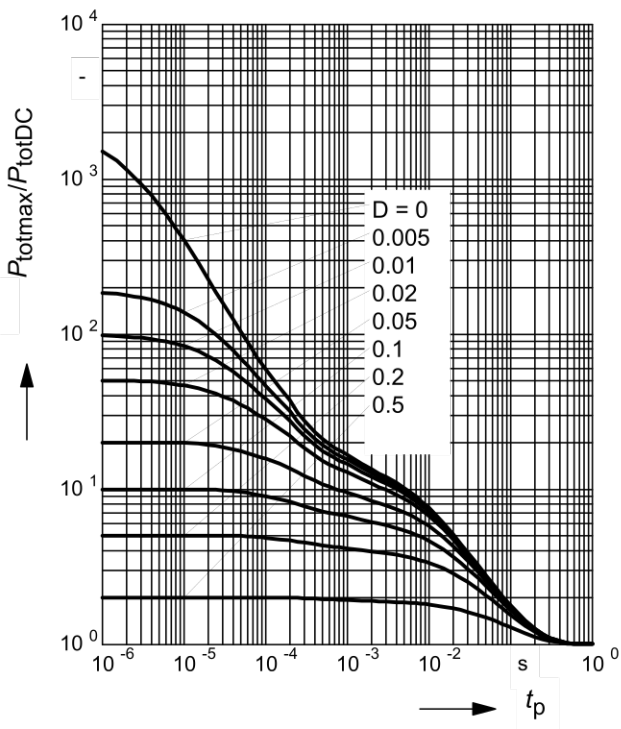

3

Total power dissipation $P_{tot} = f(T_S)$
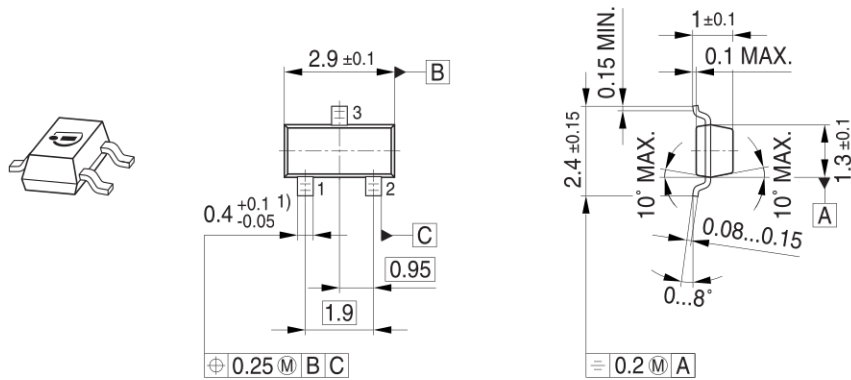
Permissible Pulse Load $R_{thJS} = f(t_p)$

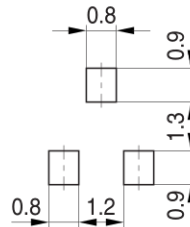**Permissible Pulse Load**

$P_{totmax}/P_{totDC} = f(t_p)$

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Package Outline

1) Lead width can be 0.6 max. in dambar area

Foot Print
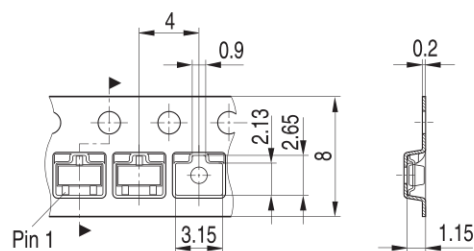

Marking Layout (Example)

Manufacturer

2005, June
Date code (YM)

Pin 1

BCW66
Type code

Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel

Pin 1

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